



175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	Ι_D Τ _C = +25°C
-30V	7.5 m Ω @ V _{GS} = -10V	-50A
-30 V	$10m\Omega$ @ $V_{GS} = -4.5V$	-45A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

Features and Benefits

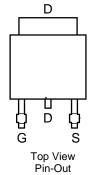
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- · Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

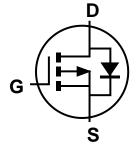
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.33 grams (Approximate)









Equivalent Circuit

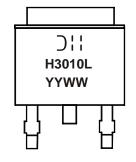
Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH3010LK3-13	TO252	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Oll = Manufacturer's Marking
H3010L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 15 = 2015)
WW = Week (01 to 53)

DMPH3010LK3 Document number: DS38123 Rev. 1 - 2 1 of 7

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Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Prais Correct (Note C) V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	-50 -40	А
Continuous Drain Current (Note 6), V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	-16 -11	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-100	Α		
Maximum Body Diode Continuous Current (Note 6)	Is	-3.5	Α		
Avalanche Current (Note 7), L = 0.1mH	I _{AS}	-47	Α		
Avalanche Energy (Note 7), L = 0.1mH	E _{AS}	113	mJ		

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	73	°C/W
Total Power Dissipation (Note 6)		P _D	3.9	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	38	°C/W	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	1.0	C/VV
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C	

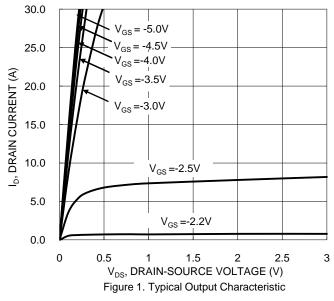
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

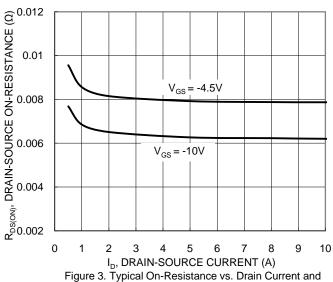
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	1	-	-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	-		±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	D	-	5.7	7.5	mΩ	$V_{GS} = -10V, I_D = -10A$
Static Dialii-Source Off-Resistance	R _{DS(ON)}	-	7.2	10	11122	$V_{GS} = -4.5V, I_{D} = -10A$
Diode Forward Voltage	V_{SD}	-	-0.65	-1.0	V	$V_{GS} = 0V$, $I_S = -1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	1	6807	1	pF	45)/)/ 0)/
Output Capacitance	Coss	-	988	-	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	647	_	pF	1 = 1.0Wii iz
Gate Resistance	R_g	-	6.2	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	66	_	nC	
Total Gate Charge (V _{GS} = -10V)	Q_g	-	139	-	nC	\/ 15\/ I- 10A
Gate-Source Charge	Q_{gs}	1	19.1		nC	$V_{DS} = -15V, I_{D} = -10A$
Gate-Drain Charge	Q_{gd}	-	21.7	_	nC]
Turn-On Delay Time	t _{D(ON)}		9.0	_	ns	
Turn-On Rise Time	t _R	_	10.5		ns	$V_{DS} = -15V, V_{GEN} = -10V,$
Turn-Off Delay Time	t _{D(OFF)}		255	_	ns	$R_G = 6\Omega$, $I_D = -1A$
Turn-Off Fall Time	t _F	_	95	_	ns	7
Body Diode Reverse Recovery Time	t _{RR}	_	27	_	ns	I _F = -10A, di/dt = -100A/μs
Body Diode Reverse Recovery Charge	Q_{RR}	_	21	_	nC	I _F = -10A, di/dt = -100A/μs

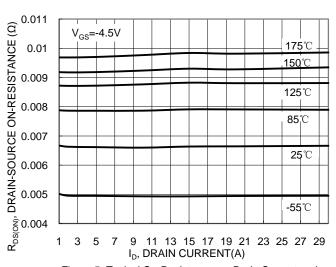
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J =+ 25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.









Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

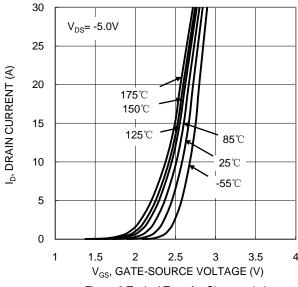
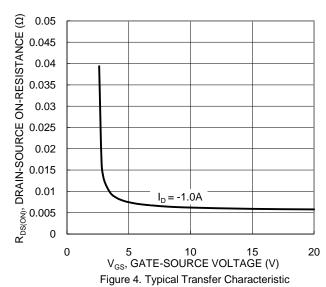


Figure 2. Typical Transfer Characteristic



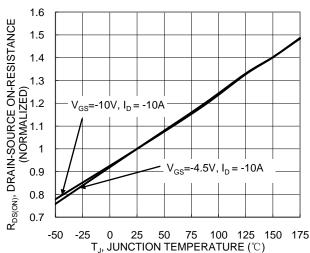


Figure 6. On-Resistance Variation with Temperature



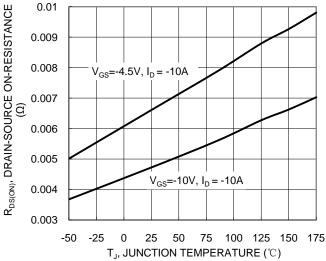
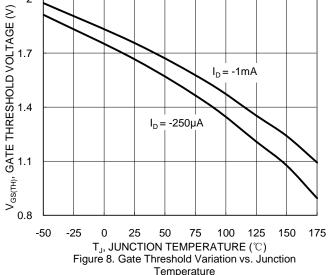


Figure 7. On-Resistance Variation with Temperature



Temperature

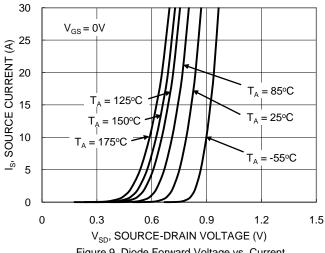
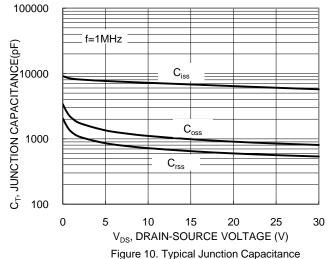
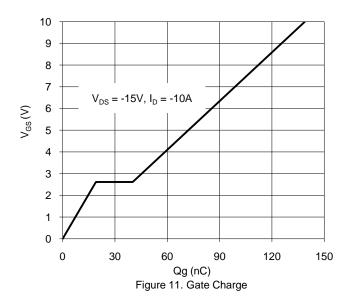


Figure 9. Diode Forward Voltage vs. Current





1000 R_{DS(ON)} Limited $P_W = 10 \mu s$ $P_w = 100 \mu s$ I_D, DRAIN CURRENT (A) $P_W = 10 \text{m/s}$ P_W =100ms Single Pulse $P_W = 1s$ DUT on Infinite Heatsink V_{GS}= -10V 1 0.1 10 100 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



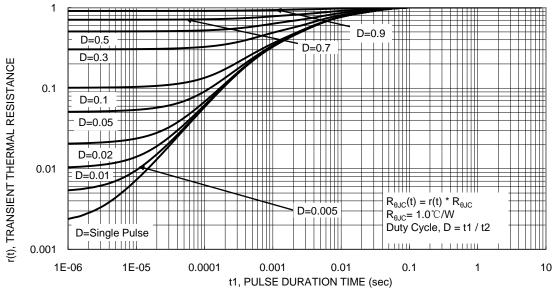


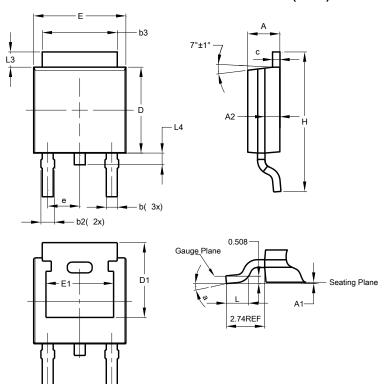
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

TO252 (DPAK)

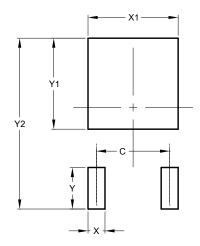


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
C	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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